

forming a P-layer of P-type nitrogen-III Group compound semiconductor satisfying formula $Al_xGa_yIn_{1-x-y}N$; and
forming between said N-layer and said P-layer a middle layer of nitrogen-III Group compound semiconductor satisfying the formula $Al_xGa_yIn_{1-x-y}N$, said middle layer being doped with a P-type dopant.

17. The method according to claim 16, wherein said middle layer comprises a Zn-doped layer.--

REMARKS

The Applicant believes that the claims are in condition for allowance and requests that the application be processed to issue. If any questions remain, the Examiner is respectfully invited to contact the undersigned.

Meanwhile, please note the attached form PTO-1449 and listed documents and return a copy of that form initialed per MPEP 609.

Respectfully submitted,

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